DSC7Q01

Silicon NPN epitaxial planar type darlington

For low frequency output amplification Darlington connection DSC8Q01 in MiniP3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

DSC7Q01×0L Embossed type (Thermo-compression sealing): 1000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	100	V	
Collector-emitter voltage (Base open)	V_{CEO}	80	V	
Emitter-base voltage (Collector open)	V_{EBO}	5	V	
Collector current	I_{C}	1	A	
Peak collector current	I_{CP}	1.5	A	
Collector power dissipation	P _C	1	W	
Junction temperature	T_j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

Absolute maximum rating without heat sink for P_C is 0.5 W

■ Package

• Code

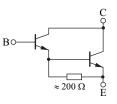
MiniP3-F2-B

Package dimension clicks here. \rightarrow

Pin Name

- 1. Base
- 2. Collector
- 3. Emitter

■ Marking Symbol: 5K



■ Electrical Characteristics $T_a = 25$ °C±3°C

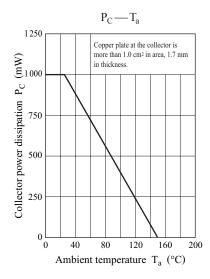
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	100			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_{E} = 0$			0.1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 4 \text{ V}, I_C = 0$			0.1	μΑ
Forward current transfer ratio *1,2	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}$	4000		40 000	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = 1 \text{ A}, I_{\rm B} = 1 \text{ mA}$			1.8	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			2.2	V

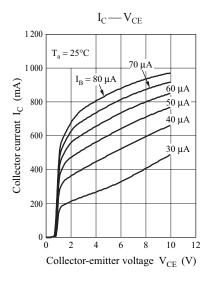
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

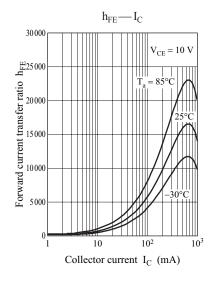
- 2. *1: Pulse measurement
 - *2: Rank classification

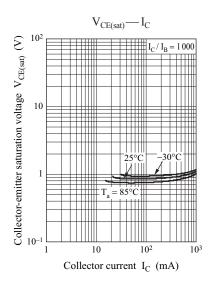
Code	Q	R	S	0
Rank	Q	R	S	No-rank
h_{FE}	4000 to 10000	8000 to 20000	16000 to 40000	4 000 to 40 000
Marking Symbol	5KQ	5KR	5KS	5K

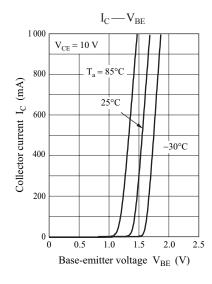
Product of no-rank is not classified and have no marking symbol for rank.

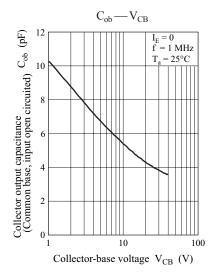


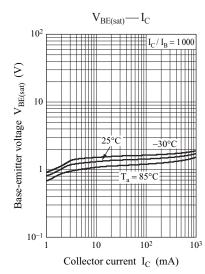












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